



# Voidless Hermetically Sealed Unidirectional Transient Voltage Suppressors

Qualified per MIL-PRF-19500/551

Qualified Levels: JAN, JANTX, and JANTXV

## **DESCRIPTION**

This surface mount series of 500 watt voidless hermetically sealed unidirectional Transient Voltage Suppressors (TVS) are military qualified to MIL-PRF-19500/551 and are ideal for high-reliability applications where a failure cannot be tolerated. Working peak "standoff" voltages are available from 5.0 to 51.6 volts. They are very robust, using a hard glass casing and internal Category 1 metallurgical bonds. These devices are also available in axial-leaded packages for thru-hole mounting.

**Important:** For the latest information, visit our website <a href="http://www.microsemi.com">http://www.microsemi.com</a>.

#### **FEATURES**

- Surface mount equivalent of JEDEC registered 1N6461 thru 1N6468 series.
- Available as 500 watt peak pulse power (P<sub>PP</sub>).
- Working peak "standoff" voltage (V<sub>WM</sub>) from 5.0 to 51.6 volt.
- High surge current and peak pulse power provides transient voltage protection for sensitive circuits.
- Triple-layer passivation.
- Internal "Category 1" metallurgical bonds.
- Voidless hermetically sealed glass package.
- JAN, JANTX, and JANTXV qualifications available per MIL-PRF-19500/551. Other screening in reference to MIL-PRF-19500 is also available.

(See <u>part nomenclature</u> for all available options.)

RoHS compliant versions available (commercial grade only).

#### **APPLICATIONS / BENEFITS**

- Military and other high-reliability applications.
- Extremely robust construction.
- ESD and EFT protection per IEC61000-4-2 and IEC61000-4-4 respectively.
- Protection from secondary effects of lightning per select levels in IEC61000-4-5.
- Square-end-cap terminals for easy placement.
- Nonsensitive to ESD per MIL-STD-750 method 1020.
- Inherently radiation hard as described in Microsemi "MicroNote 050".

## MAXIMUM RATINGS @ 25 °C

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T <sub>J</sub> and T <sub>STG</sub>	-55 to +175	°C
Thermal Resistance, Junction to Endcap	R <sub>OJEC</sub>	20	°C/W
Forward Surge Current @ 8.3 ms half-sine	I <sub>FSM</sub>	80	Α
Forward Voltage @ 1 Amp	V <sub>F</sub>	1.5	V
Peak Pulse Power @ 10/1000 μs	P <sub>PP</sub>	500	W
Reverse Power Dissipation (1)	P <sub>R</sub>	2.5	W
Solder Temperature @ 10 s		260	°C

Notes: 1. Derate at 50 mW/°C (see figure 4).



"B" SQ-MELF Package

## Also available in:

"B" Package (axial –leaded) 1N6461 - 1N6468

## MSC - Lawrence

6 Lake Street, Lawrence, MA 01841 Tel: 1-800-446-1158 or (978) 620-2600 Fax: (978) 689-0803

#### MSC - Ireland

Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

#### Website:

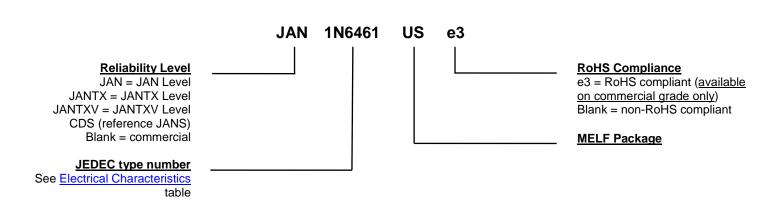
www.microsemi.com



## **MECHANICAL and PACKAGING**

- CASE: Hermetically sealed voidless hard glass with tungsten slugs.
- TERMINALS: Axial-leads are tin/lead over copper. RoHS compliant matte-tin is available for commercial grade only.
- MARKING: Body paint and part number.
- POLARITY: Cathode band.
- TAPE & REEL option: Standard per EIA-296. Contact factory for quantities.
- WEIGHT: Approximately 750 milligrams.
- See <u>Package Dimensions</u> on last page.

## PART NOMENCLATURE



SYMBOLS & DEFINITIONS				
Symbol	Definition			
αv(BR)	Temperature Coefficient of Breakdown Voltage: The change in breakdown voltage divided by the change in temperature expressed in %/°C or mV/°C.			
$V_{(BR)}$	Breakdown Voltage: The voltage across the device at a specified current I <sub>(BR)</sub> in the breakdown region.			
V <sub>WM</sub>	Rated working standoff voltage: The maximum-rated value of dc or repetitive peak positive cathode-to-anode voltage that may be continuously applied over the standard operating temperature.			
I <sub>D</sub>	Standby Current: The current through the device at rated stand-off voltage.			
I <sub>PP</sub>	Peak Impulse Current: The maximum rated random recurring peak impulse current or nonrepetitive peak impulse current that may be applied to a device. A random recurring or nonrepetitive transient current is usually due to an external cause, and it is assumed that its effect will have completely disappeared before the next transient arrives.			
V <sub>C</sub>	Clamping Voltage: The voltage across the device in a region of low differential resistance during the application of an impulse current (I <sub>PP</sub> ) for a specified waveform.			
P <sub>PP</sub>	Peak Pulse Power. The rated random recurring peak impulse power or rated nonrepetitive peak impulse power. The impulse power is the maximum-rated value of the product of I <sub>PP</sub> and V <sub>C</sub> .			



# **ELECTRICAL CHARACTERISTICS**

TYPE	MINIMUM BREAK DOWN VOLTAGE V <sub>(BR)</sub>	BREAKDOWN CURRENT I (BR)	RATED WORKING STANDOFF VOLTAGE V <sub>WM</sub>	MAXIMUM STANDBY CURRENT I <sub>D</sub> @ V <sub>RWM</sub>	MAXIMUM CLAMPING VOLTAGE V <sub>C</sub> @ 10/1000 µs	PEAK II CUR	IMUM MPULSE RENT PP	MAXIMUM TEMP. COEF. OF αν(BR)
	@ I <sub>(BR)</sub>					@ 8/20 µs	@ 10/1000 µs	
	Volts	mA	V (pk)	μА	V (pk)	A (pk)	A (pk)	%/°C
1N6461US	5.6	25	5	3000	9.0	315	56	-0.03, +0.045
1N6462US	6.5	20	6	2500	11.0	258	46	+0.060
1N6463US	13.6	5	12	500	22.6	125	22	+0.085
1N6464US	16.4	5	15	500	26.5	107	19	+0.085
1N6465US	27.0	2	24	50	41.4	69	12	+0.096
1N6466US	33.0	1	30.5	3	47.5	63	11	+0.098
1N6467US	43.7	1	40.3	2	63.5	45	8	+0.101
1N6468US	54.0	1	51.6	2	78.5	35	6	+0.103



## **GRAPHS**

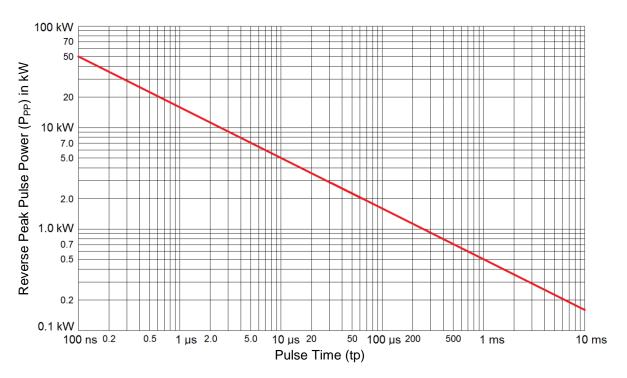


FIGURE 1
Peak Pulse Power vs Pulse Time

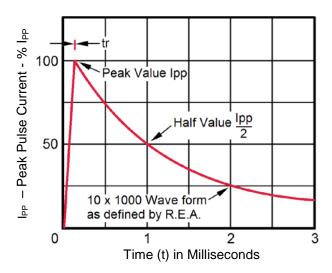


FIGURE 2 10/1000 µs Current Impulse Waveform



## **GRAPHS**

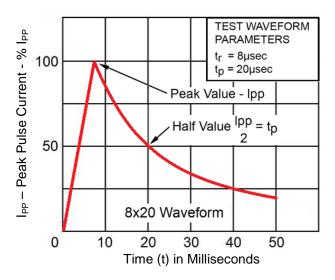
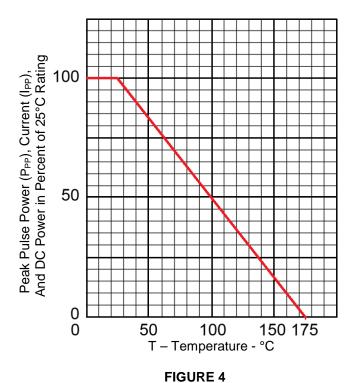


FIGURE 3 8/20 µs Current Impulse Waveform

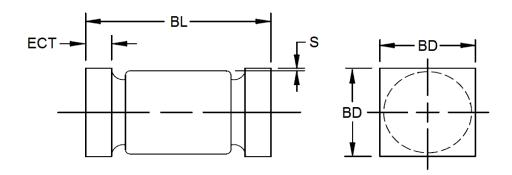


T4-LDS-0286-1, Rev. 1 (4/24/13)

**Derating Curve** 



## **PACKAGE DIMENSIONS**

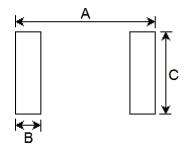


	In	ch	Millimeters		
	Min Max		Min	Max	
BD	0.137	0.148	3.48	3.76	
BL	0.200	0.225	5.08	5.72	
ECT	0.019	0.028	0.48	0.71	
S	0.003		0.08		

#### NOTES:

- 1. Dimensions are in inches.
- Millimeter equivalents are given for information only.
   Referencing to dimension S, minimum clearance of glass body to mounting surface on all orientations.
- 4. Dimensions are pre-solider dip.
- In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi x$  symbology.

## **PAD LAYOUT**



	INCH	MILLIMETERS
Α	0.288	7.32
В	0.070	1.78
С	0.155	3.94

Note: If mounting requires adhesive separate from the solder, an additional 0.080 inch diameter contact may be placed in the center between the pads as an optional spot for cement.